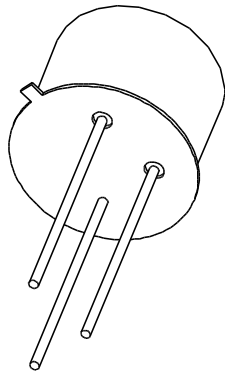


DATA SHEET



BSX45; BSX46; BSX47 NPN medium power transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Apr 23

NPN medium power transistors

BSX45; BSX46; BSX47

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

- General industrial applications.

DESCRIPTION

NPN medium power transistor in a TO-39 metal package.

PINNING

| PIN | DESCRIPTION |
|-----|------------------------------|
| 1 | emitter |
| 2 | base |
| 3 | collector, connected to case |

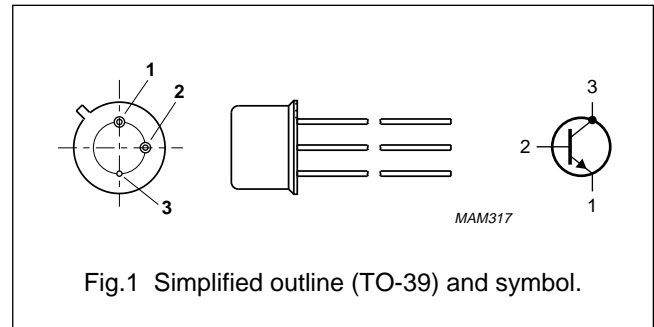


Fig.1 Simplified outline (TO-39) and symbol.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|------------------|------------------------------|---|------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | | | | |
| | BSX45 | | – | – | 80 | V |
| | BSX46 | | – | – | 100 | V |
| V _{CEO} | collector-emitter voltage | open base | | | | |
| | BSX45 | | – | – | 40 | V |
| | BSX46 | | – | – | 60 | V |
| | BSX47 | | – | – | 80 | V |
| I _{CM} | peak collector current | | – | – | 1.5 | A |
| P _{tot} | total power dissipation | T _{case} ≤ 25 °C | – | – | 6.25 | W |
| h _{FE} | DC current gain | I _C = 100 mA; V _{CE} = 1 V | | | | |
| | BSX45-10; BSX46-10; BSX47-10 | | 63 | 100 | 160 | |
| | BSX45-16; BSX46-16; BSX47-16 | | 100 | 160 | 250 | |
| f _T | transition frequency | I _C = 50 mA; V _{CE} = 10 V; f = 100 MHz | 50 | – | – | MHz |

NPN medium power transistors

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|---------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | | | |
| | BSX45 | | – | 80 | V |
| | BSX46 | | – | 100 | V |
| | BSX47 | | – | 120 | V |
| V _{CEO} | collector-emitter voltage | open base | | | |
| | BSX45 | | – | 40 | V |
| | BSX46 | | – | 60 | V |
| | BSX47 | | – | 80 | V |
| V _{EBO} | emitter-base voltage | open collector | – | 7 | V |
| I _C | collector current (DC) | | – | 1 | A |
| I _{CM} | peak collector current | | – | 1.5 | A |
| I _{BM} | peak base current | | – | 200 | mA |
| P _{tot} | total power dissipation | T _{case} ≤ 25 °C | – | 6.25 | W |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 200 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|-------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | in free air | 200 | K/W |
| R _{th j-c} | thermal resistance from junction to case | | 28 | K/W |

NPN medium power transistors

BSX45; BSX46; BSX47

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|------|------|------|---------------|
| I_{CBO} | collector cut-off current BSX45; BSX46 | $I_E = 0; V_{CB} = 60\text{ V}$ | – | – | 30 | nA |
| | | $I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 150\text{ °C}$ | – | – | 10 | μA |
| I_{CBO} | collector cut-off current BSX47 | $I_E = 0; V_{CB} = 80\text{ V}$ | – | – | 30 | nA |
| | | $I_E = 0; V_{CB} = 80\text{ V}; T_{amb} = 150\text{ °}$ | – | – | 10 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 5\text{ V}$ | – | – | 10 | nA |
| h_{FE} | DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16 | $I_C = 100\text{ }\mu\text{A}; V_{CE} = 1\text{ V}$ | 15 | 40 | – | |
| | | | 25 | 90 | – | |
| h_{FE} | DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16; BSX47-16 | $I_C = 100\text{ mA}; V_{CE} = 1\text{ V}$ | 63 | 100 | 160 | |
| | | | 100 | 160 | 250 | |
| h_{FE} | DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16 | $I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$ | 25 | 40 | – | |
| | | | 35 | 60 | – | |
| h_{FE} | DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16 | $I_C = 1\text{ A}; V_{CE} = 1\text{ V}$ | – | 20 | – | |
| | | | – | 30 | – | |
| V_{CEsat} | collector-emitter saturation voltage BSX45; BSX46 | $I_C = 1\text{ A}; I_B = 100\text{ mA}$ | – | – | 1 | V |
| V_{CEsat} | collector-emitter saturation voltage BSX47 | $I_C = 500\text{ mA}; I_B = 25\text{ mA}$ | – | – | 900 | mV |
| V_{BE} | base-emitter voltage | $I_C = 100\text{ mA}; V_{CE} = 1\text{ V}$ | – | – | 1 | V |
| | | $I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$ | 0.75 | – | 1.5 | V |
| | | $I_C = 1\text{ A}; V_{CE} = 1\text{ V}$ | – | – | 2 | V |
| C_c | collector capacitance BSX45 BSX46 BSX47 | $I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$ | – | – | 25 | pF |
| | | | – | – | 20 | pF |
| | | | – | – | 15 | pF |
| C_e | emitter capacitance | $I_C = I_C = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$ | – | – | 80 | pF |
| f_T | transition frequency | $I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$ | 50 | – | – | MHz |
| F | noise figure | $I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 1\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$ | – | 3.5 | – | dB |
| Switching times (between 10% and 90% levels) | | | | | | |
| t_{on} | turn-on time | $I_{Con} = 100\text{ mA}; I_{Bon} = 5\text{ mA};$ $I_{Boff} = -5\text{ mA}$ | – | – | 200 | ns |
| t_{off} | turn-off time | | – | – | 850 | ns |

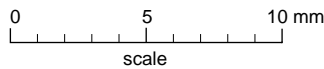
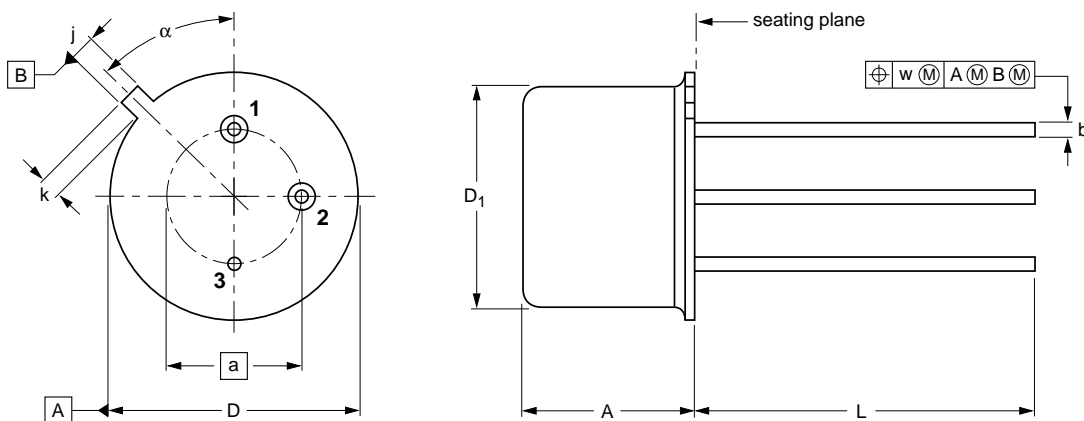
NPN medium power transistors

BSX45; BSX46; BSX47

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

| UNIT | A | a | b | D | D ₁ | j | k | L | w | α |
|------|--------------|------|--------------|--------------|----------------|--------------|--------------|--------------|-----|-----|
| mm | 6.60 6.35 | 5.08 | 0.48 0.41 | 9.39 9.08 | 8.33 8.18 | 0.85 0.75 | 0.95 0.75 | 14.2 12.7 | 0.2 | 45° |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT5/11 | | TO-39 | | | | 97-04-11 |

NPN medium power transistors

BSX45; BSX46; BSX47

DEFINITIONS

| Data Sheet Status | |
|---|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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NPN medium power transistors

BSX45; BSX46; BSX47

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